4-Bit 24 Mb/s Dual-Supply Level Translator

The NLSX4378A is a 4-bit configurable dual-supply bidirectional auto sensing translator that does not require a directional control pin. The V_{CC} I/O and V_L I/O ports are designed to track two different power supply rails, V_{CC} and V_L respectively. The V_{CC} and V_L supply rails are configurable from 1.65 V to 5.5 V. This allows voltage logic signals on the V_L side to be translated into lower, higher or equal value voltage logic signals on the V_{CC} side, and vice-versa.

The NLSX4378A translator has open–drain outputs with integrated 10 k Ω pullup resistors on the I/O lines. The integrated pullup resistors are used to pullup the I/O lines to either V_L or V_{CC}. The NLSX4378A is an excellent match for open–drain applications such as the I²C communication bus.

Features

- V_L can be Less than, Greater than or Equal to V_{CC}
- Wide V_{CC} Operating Range: 1.65 V to 5.5 V Wide V_L Operating Range: 1.65 V to 5.5 V
- High-Speed with 24 Mb/s Guaranteed Date Rate
- Low Bit-to-Bit Skew
- Enable Input is Overvoltage Tolerant (OVT) to 5.5 V
- Nonpreferential Powerup Sequencing
- Integrated 10 kΩ Pullup Resistors
- ESD Protection: >7 kV HBM for all pins
- Small Space Saving Package 2.02 x 1.54 mm µBump12
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

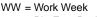
- I²C, SMBus, PMBus
- Low Voltage ASIC Level Translation
- Mobile Phones, PDAs, Cameras



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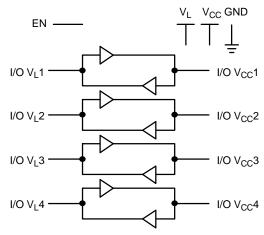
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= Pb-Free Package

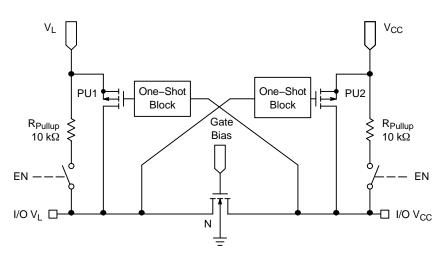




ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 8 of this data sheet.

1





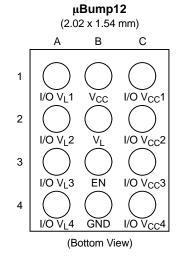
PIN ASSIGNMENT

Pins	Description
V _{CC}	V _{CC} Input Voltage
VL	V _L Input Voltage
GND	Ground
EN	Output Enable
I/O V _{CC} n	V _{CC} I/O Port, Referenced to V _{CC}
I/O V _L n	V_L I/O Port, Referenced to V_L

FUNCTION TABLE

EN	Operating Mode	
L	Hi–Z	
Н	I/O Buses Connected	

PIN LOCATIO	PIN LOCATION					
Pin	Pin Name					
A1	I/O V _L 1					
A2	I/O V _L 2					
A3	I/O VL3					
A4	I/O VL4					
B1	V _{CC}					
B2	VL					
B3	EN					
B4	GND					
C1	I/O V _{CC} 1					
C2	I/O V _{CC} 2					
C3	I/O V _{CC} 3					
C4	I/O V _{CC} 4					



MAXIMUM RATINGS

Symbol	Parameter	Condition	Value	Unit
V _{CC}	DC Supply Voltage		-0.3 to +7.0	V
VL	DC Supply Voltage		-0.3 to +7.0	V
I/O V _{CC}	V _{CC} -Referenced DC Input/Output Voltage		-0.3 to (V _{CC} + 0.3)	V
I/O VL	V _L -Referenced DC Input/Output Voltage		–0.3 to (V _L + 0.3)	V
V _{EN}	Enable Control Pin DC Input Voltage		-0.3 to +7.0	V
I _{I/O_SC}	Short–Circuit Duration (I/O V_{L} and I/O V_{CC} to GND)	Continuous	40	mA
T _{STG}	Storage Temperature		-65 to +150	°C
I _{LU}	Latch-up Current		100	mA
ESD Rating	Human Body Model Charged Device Model		7000 2000	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Мах	Unit
V _{CC}	DC Supply Voltage	1.65	5.5	V
VL	DC Supply Voltage	1.65	5.5	V
V _{EN}	Enable Control Pin Voltage	GND	5.5	V
V _{IO}	I/O Pin Voltage	GND	V_{CC} or V_L	V
T _A	Operating Temperature Range	-55	+125	°C

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

			-	-40°C to +85°	C	–55°C to	o +125°C	
Symbol	Parameter	Test Conditions	Min	Typ (Notes 1, 2)	Max	Min	Max	Unit
VIHC	I/O V _{CC} Input HIGH Voltage		V _{CC} – 0.4	-	-	V _{CC} – 0.4	-	V
VILC	I/O V _{CC} Input LOW Voltage		-	-	0.15	-	0.15	V
VIHL	I/O V _L Input HIGH Voltage		$V_{L} - 0.4$	-	-	$V_{L} - 0.4$	-	V
V _{ILL}	I/O V _L Input LOW Voltage		-	-	0.15	-	0.15	V
V _{IH}	Control Pin Input HIGH Voltage		0.65 * V _L	-	_	0.65 * V _L	-	V
V_{IL}	Control Pin Input LOW Voltage		-	-	0.35 * V _L	-	0.35 * V _L	V
V _{OHC}	I/O V _{CC} Output HIGH Voltage	I/O V _{CC} Source Current = $20 \ \mu A$	0.8 * V _{CC}	-	-	0.8 * V _{CC}	-	V
V _{OLC}	I/O V _{CC} Output LOW Voltage	I/O V _{CC} Sink Current = 1.0 mA, I/O_V _L \leq 0.15 V	-	-	0.4	-	0.4	V
V _{OHL}	I/O V _L Output HIGH Voltage	I/O V _L Source Current = 20 μA	0.8 * V _L	-	_	0.8 * V _L	-	V
V _{OLL}	I/O V _L Output LOW Voltage	I/O V _L Sink Current = 1.0 mA, I/O_V _{CC} \leq 0.15 V	_	-	0.4	_	0.4	V
I _{QVCC}	V _{CC} Supply Current	I/O V _{CC} and I/O V _L Unconnected, V _{EN} = V _L	-	0.5	2.0	-	3.0	μΑ
I _{QVL}	V _L Supply Current	I/O V _{CC} and I/O V _L Unconnected, V _{EN} = V _L	_	0.3	1.0	_	3.0	μΑ
I _{TS-VCC}	V _{CC} Tristate Output Mode Supply Current	I/O V _{CC} and I/O V _L Unconnected, V _{EN} = GND	_	0.1	1.0	_	1.5	μΑ
I _{TS-VL}	V _L Tristate Output Mode Supply Current	I/O V _{CC} and I/O V _L Unconnected, V _{EN} = GND	_	0.1	1.0	_	1.5	μΑ
I _{OZ}	I/O Tristate Output Mode Leakage Current	T _A = +25°C	_	0.1	1.0	_	1.0	μΑ
R _{PU}	Pullup Resistor I/O V_L and V_{CC}	T _A = +25°C	-	10	-	-	-	kΩ

DC ELECTRICAL CHARACTERISTICS (V_{CC} = 1.65 V to 5.5 V and V_{L} = 1.65	V to 5.5 V, unless otherwise specified)
---	---

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 1. Typical values are for $V_{CC} = +2.8 \text{ V}$, $V_L = +1.8 \text{ V}$ and $T_A = +25^{\circ}\text{C}$. 2. All units are production tested at $T_A = +25^{\circ}\text{C}$. Limits over the operating temperature range are guaranteed by design.

TIMING CHARACTERISTICS – RAIL-TO-RAIL DRIVING CONFIGURATIONS

(I/O test circuit of Figures 2 and 3, C_{LOAD} = 15 pF, driver output impedance \leq 50 Ω , R_{LOAD} = 1 M Ω)

			-40°C to +85°C (Note 3)			-55°C to +125°C (Note 3)		
Symbol	Parameter	Test Conditions	Min	Тур	Max	Min	Max	Unit
V _L = 1.65 V,	V _{CC} = 5.5 V							
t _{RVCC}	I/O V _{CC} Risetime				15		15	ns
t _{FVCC}	I/O V _{CC} Falltime				30		30	ns
t _{RVL}	I/O V _L Risetime				30		30	ns
t _{FVL}	I/O V _L Falltime				10		10	ns
t _{PDVL-VCC}	Propagation Delay (Driving I/O V_L)				20		20	ns
t _{PDVCC-VL}	Propagation Delay (Driving I/O V_{CC})				20		20	ns
t _{SKEW}	Channel-to-Channel Skew				5		5	nS
MDR	Maximum Data Rate		24			24		Mb/s
V _L = 1.8 V, V	V _{CC} = 2.8 V							
t _{RVCC}	I/O V _{CC} Risetime				15		15	ns
t _{FVCC}	I/O V _{CC} Falltime				15		15	ns
t _{RVL}	I/O V _L Risetime				25		25	ns
t _{FVL}	I/O V _L Falltime				10		10	ns
t _{PDVL-VCC}	Propagation Delay (Driving I/O V_L)				15		15	ns
t _{PDVCC-VL}	Propagation Delay (Driving I/O V_{CC})				15		15	ns
t _{SKEW}	Channel-to-Channel Skew				5		5	nS
MDR	Maximum Data Rate		24			24		Mb/s
V _L = 2.5 V, V	V _{CC} = 3.6 V							
t _{RVCC}	I/O V _{CC} Risetime				15		15	ns
t _{FVCC}	I/O V _{CC} Falltime				10		10	ns
t _{RVL}	I/O V _L Risetime				15		15	ns
t _{FVL}	I/O V _L Falltime				10		10	ns
t _{PDVL-VCC}	Propagation Delay (Driving I/O V_L)				15		15	ns
t _{PDVCC-VL}	Propagation Delay (Driving I/O V_{CC})				15		15	ns
t _{SKEW}	Channel-to-Channel Skew				5		5	nS
MDR	Maximum Data Rate		24			24		Mb/s
V _L = 2.8 V, V	V _{CC} = 1.8 V					•		
t _{RVCC}	I/O V _{CC} Risetime				25		25	ns
t _{FVCC}	I/O V _{CC} Falltime				10		10	ns
t _{RVL}	I/O V _L Risetime				15		15	ns
t _{FVL}	I/O V _L Falltime				15		15	ns
t _{PDVL-VCC}	Propagation Delay (Driving I/O V_L)				15		15	ns
t _{PDVCC-VL}	Propagation Delay (Driving I/O V_{CC})				15		15	ns
t _{SKEW}	Channel-to-Channel Skew				5		5	nS
MDR	Maximum Data Rate		24			24		Mb/s

3. Limits over the operating temperature range are guaranteed by design.

TIMING CHARACTERISTICS – RAIL-TO-RAIL DRIVING CONFIGURATIONS

(I/O test circuit of Figures 2 and 3, C_{LOAD} = 15 pF, driver output impedance \leq 50 Ω , R_{LOAD} = 1 M Ω)

			-40°C to +85°C (Note 3)			-55°C to +125°C (Note 3)		
Symbol	Parameter	Test Conditions	Min	Тур	Max	Min	Max	Unit
V _L = 3.6 V, \	/ _{CC} = 2.5 V				•			
t _{RVCC}	I/O V _{CC} Risetime				15		15	ns
t _{FVCC}	I/O V _{CC} Falltime				10		10	ns
t _{RVL}	I/O V _L Risetime				15		15	ns
t _{FVL}	I/O V _L Falltime				10		10	ns
t _{PDVL-VCC}	Propagation Delay (Driving I/O V_L)				15		15	ns
t _{PDVCC-VL}	Propagation Delay (Driving I/O V_{CC})				15		15	ns
t _{SKEW}	Channel-to-Channel Skew				5		5	nS
MDR	Maximum Data Rate		24			24		Mb/s
V _L = 5.5 V, \	/ _{CC} = 1.65 V							-
t _{RVCC}	I/O V _{CC} Risetime				30		30	ns
t _{FVCC}	I/O V _{CC} Falltime				10		10	ns
t _{RVL}	I/O V _L Risetime				15		15	ns
t _{FVL}	I/O V _L Falltime				30		30	ns
t _{PDVL-VCC}	Propagation Delay (Driving I/O V_L)				20		20	ns
t _{PDVCC-VL}	Propagation Delay (Driving I/O V_{CC})				20		20	ns
t _{SKEW}	Channel-to-Channel Skew				5		5	nS
MDR	Maximum Data Rate		24			24		Mb/s

3. Limits over the operating temperature range are guaranteed by design.

TIMING CHARACTERISTICS - OPEN DRAIN DRIVING CONFIGURATIONS

(I/O test circuit of Figures 4 and 5, C_{LOAD} = 15 pF, driver output impedance \leq 50 Ω , R_{LOAD} = 1 M Ω)

			-40°C to +85°C (Note 4)		°C	-55°C to +125°C (Note 4)		
Symbol	Parameter	Test Conditions	Min	Тур	Max	Min	Max	Unit
+1.65 \leq V _L ,	V _{CC} ≤ +5.5 V	•						
t _{RVCC}	I/O V _{CC} Risetime				400		400	ns
t _{FVCC}	I/O V _{CC} Falltime				50		50	ns
t _{RVL}	I/O V _L Risetime				400		400	ns
t _{FVL}	I/O V _L Falltime				60		60	ns
t _{PDVL-VCC}	Propagation Delay (Driving I/O V_L)				1000		1000	ns
t _{PDVCC-VL}	Propagation Delay (Driving I/O V_{CC})				1000		1000	ns
t _{SKEW}	Channel-to-Channel Skew				50		50	nS
MDR	Maximum Data Rate		2			2		Mb/s

4. Limits over the operating temperature range are guaranteed by design.

TEST SETUPS

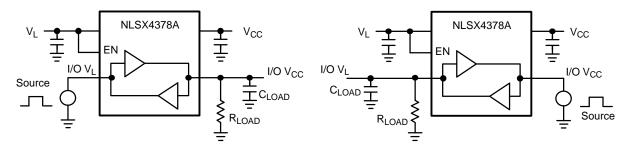




Figure 3. Rail-to-Rail Driving I/O V_{CC}

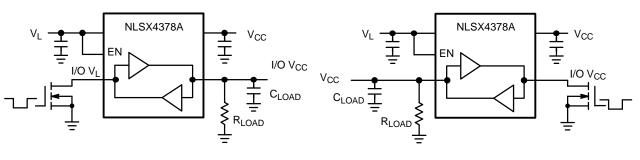


Figure 4. Open–Drain Driving I/O VL

Figure 5. Open–Drain Driving I/O V_{CC}

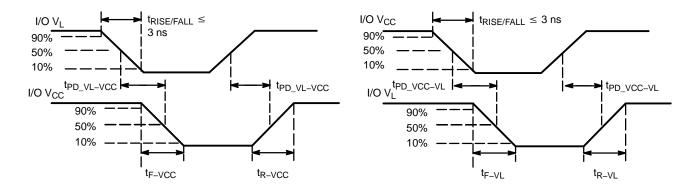


Figure 6. Definition of Timing Specification Parameters

APPLICATIONS INFORMATION

Level Translator Architecture

The NLSX4378A auto sense translator provides bi-directional voltage level shifting to transfer data in multiple supply voltage systems. This device has two supply voltages, V_L and V_{CC} , which set the logic levels on the input and output sides of the translator. When used to transfer data from the V_L to the V_{CC} ports, input signals referenced to the V_L supply are translated to output signals with a logic level matched to V_{CC} . In a similar manner, the V_{CC} to V_L translation shifts input signals with a logic level compatible to V_{CC} to an output signal matched to V_L .

The NLSX4378A consists of four bi-directional channels that independently determine the direction of the data flow without requiring a directional pin. The one-shot circuits are used to detect the rising input signals. In addition, the one shots decrease the rise time of the output signal for low-to-high transitions.

Each input/output pin has an internal 10 k Ω pull-up resistor. The magnitude of the pull-up resistors can be reduced by connecting external resistors in parallel to the internal 10 k Ω resistors.

Input Driver Requirements

The rise (t_R) and fall (t_F) timing parameters of the open drain outputs depend on the magnitude of the pull-up resistors. In addition, the propagation times (t_{PD}) , skew (t_{SKEW}) and maximum data rate depend on the impedance of the device that is connected to the translator. The timing parameters listed in the data sheet assume that the output impedance of the drivers connected to the translator is less than 50 Ω .

Enable Input (EN)

The NLSX4378A has an Enable pin (EN) that provides tri-state operation at the I/O pins. Driving the Enable pin to a low logic level minimizes the power consumption of the device and drives the I/O V_{CC} and I/O V_L pins to a high impedance state. Normal translation operation occurs when the EN pin is equal to a logic high signal. The EN pin is referenced to the V_L supply and has Overvoltage Tolerant (OVT) protection.

Power Supply Guidelines

During normal operation, supply voltage V_L can be greater than, less than or equal to V_{CC} . The sequencing of the power supplies will not damage the device during the power up operation.

For optimal performance, 0.01 μ F to 0.1 μ F decoupling capacitors should be used on the V_L and V_{CC} power supply pins. Ceramic capacitors are a good design choice to filter and bypass any noise signals on the voltage lines to the ground plane of the PCB. The noise immunity will be maximized by placing the capacitors as close as possible to the supply and ground pins, along with minimizing the PCB connection traces.

ORDERING INFORMATION

Device	Package	Shipping [†]
NLSX4378ABFCT1G	μBump12 (Backside Laminate Coating) (Pb–Free)	3000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

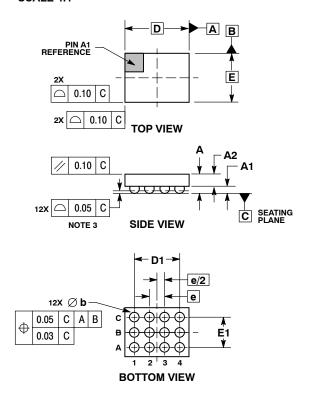




12 PIN FLIP-CHIP, 2.02x1.54, 0.5P CASE 499AU-01

ISSUE O

SCALE 4:1



DATE 19 MAR 2007

NOTES:

NOTES: 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. 2. CONTROLLING DIMENSION: MILLIMETERS. 3. COPLANARITY APPLIES TO SPHERICAL CROWNS OF SOLDER BALLS.

	MILLIMETERS				
DIM	MIN	MAX			
Α		0.66			
A1	0.21	0.27			
A2	0.33	0.39			
b	0.29	0.34			
D	2.02	BSC			
D1	1.50	BSC			
Е	1.54	BSC			
E1	1.00	BSC			
е	0.50	BSC			

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